



Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
201/	21mΩ @ V _{GS} = 10V	8.5A		
30V	$35m\Omega @ V_{GS} = 4.5V$	6.6A		

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

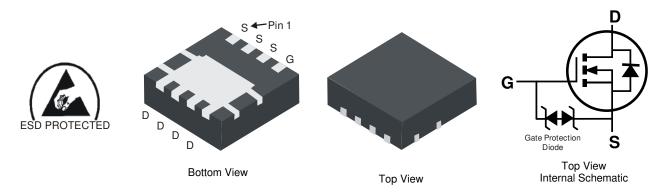
30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3018SFGQ-7	POWERDI [®] 3333-8	2000/Tape & Reel
DMN3018SFGQ-13	POWERDI [®] 3333-8	3000/Tape & Reel

Notes: 1. No

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N38 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 11 = 2011) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
	Steady State	T _A = +25°C T _A = +70°C	ID	8.5 6.8	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	11.3 9.1	А
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	6.6 5.3	А
Continuous Drain Current (Note 7) $V_{GS} = 4.5V$	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	8.7 7.0	А
Maximum Continuous Body Diode Forward Current (Note 7)			IS	2.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	60	А
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	18	А
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)		PD	1.0	W	
Thermal Resistance. Junction to Ambient (Note 6)	Steady State	D	126	°C/W	
Thermal Resistance, Junction to Amblent (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	71	C/W	
Total Power Dissipation (Note 7)		PD	2.2	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	56	°C/W	
Thermal Resistance, Junction to Amblent (Note 7)	t<10s	$R_{ heta JA}$	31		
Thermal Resistance, Junction to Case		$R_{\theta JC}$	7.0		
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)		r	r	r			
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	2.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Deserve	_	16	21	mΩ	$V_{GS} = 10V, I_D = 10A$	
	R _{DS(ON)}	—	21	35	11152	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V _{SD}	0.5	—	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	697	-	pF		
Output Capacitance	Coss	—	97	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	—	67	—	pF		
Gate Resistance	Rg	—	1.47	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	—	6.0	—	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	—	13.2	_	nC	V _{GS} = 10V, V _{DS} = 15V,	
Gate-Source Charge	Q _{gs}	—	2.2	—	nC	$I_D = 9A$	
Gate-Drain Charge	Q _{gd}	—	1.8	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.3	_	ns		
Turn-On Rise Time	t _R	_	4.4	_	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 15 Ω , I_D = 1A, R_G = 6 Ω	
Turn-Off Delay Time	t _{D(OFF)}	_	20.1	_	ns		
Turn-Off Fall Time	t _F	—	4.1	_	ns		
Reverse Recovery Time	t _{RR}	—	7.3	_	ns		
Reverse Recovery Charge	Q _{RR}	—	7.9	—	nC	- I _F = 9A, di/dt = 500A/μs	

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

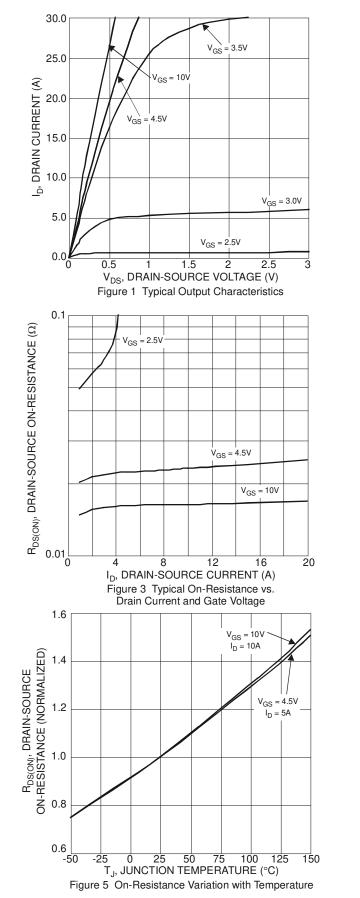
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

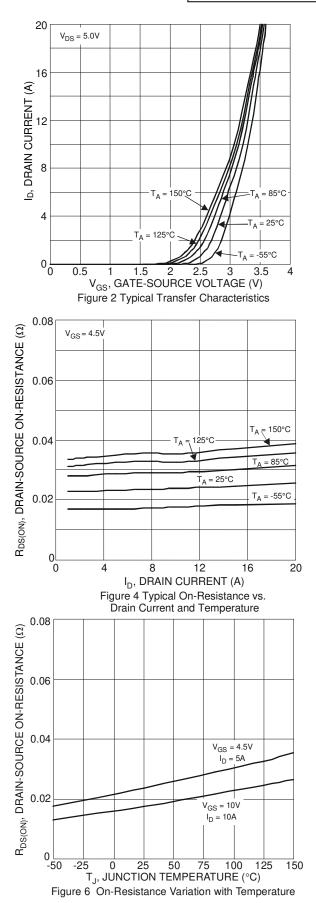
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

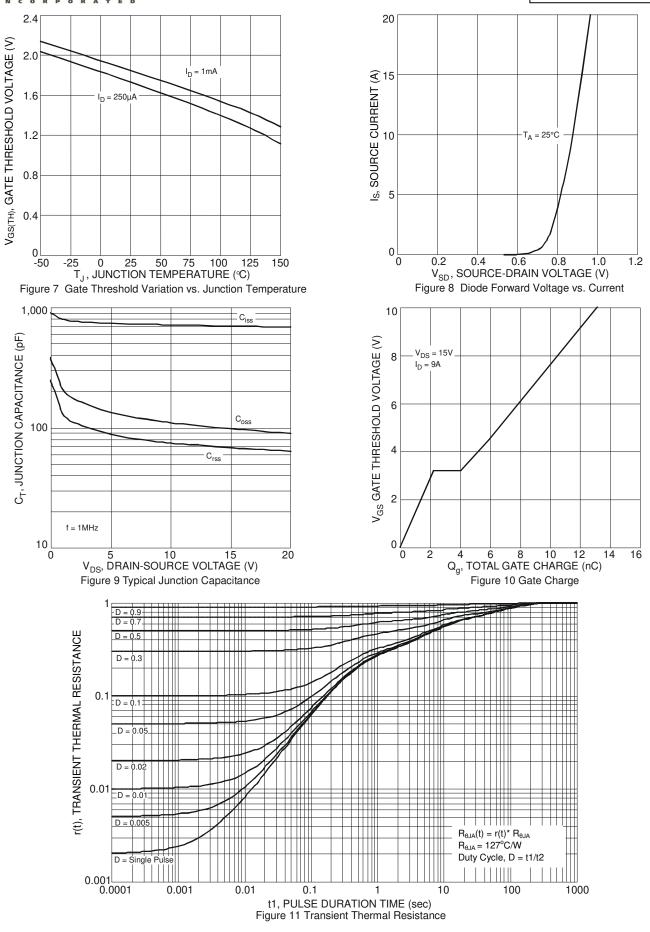








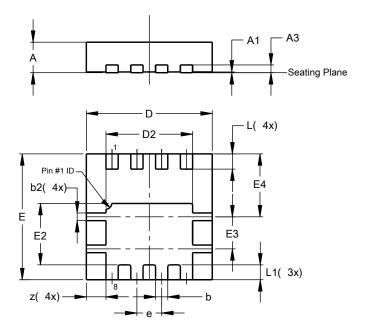
DMN3018SFGQ





Package Outline Dimensions

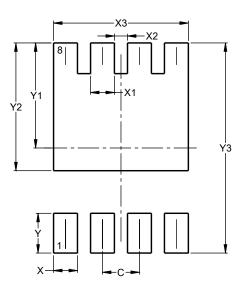
Please see http://www.diodes.com/package-outlines.html for the latest version.



POWERDI [®] 3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
ш	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
e	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	_	0.515			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



POWERDI®3333-8

POWERDI®3333-8

Dimensions	Value (in mm)			
С	0.650			
X	0.420			
X1	0.420			
X2	0.230			
X3	2.370			
Y	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			



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